

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application.

#### **Listing of Claims:**

Claims 1-24 (Canceled).

25. (Currently amended) A lower electrode of a capacitor, comprising:  
a first layer in the form of a plate comprising a material that serves as a barrier against the diffusion of impurities from a lower substrate;  
a second layer formed over the first layer, the second layer comprising a material that is easy to pattern; and  
a third layer formed over top and side surfaces of the second layer and side surfaces of the first layer, the third layer comprising a material having low leakage current properties.

26. (Original) A lower electrode of a capacitor according to claim 25, wherein the first layer comprises TiN.

27. (Original) A lower electrode of a capacitor according to claim 25, wherein the second layer comprises RuO<sub>2</sub>.

28. (Original) A lower electrode of a capacitor according to claim 26, wherein the third layer comprises Pt.

29. (New) A lower electrode of a capacitor according to claim 25, wherein the lower substrate exposed by third layer is overetched.

30. (New) A semiconductor device, comprising:  
an insulating film formed over a semiconductor substrate;  
a conductive plug formed in the insulating film;  
a first layer formed over the conductive plug and the insulating film, the first layer comprising a material that serves as a barrier against the diffusion of impurities from the conductive plug and the semiconductor substrate;  
a second layer formed over the first layer, the second layer comprising a material that is easy to pattern; and  
a third layer formed over top and side surfaces of the second layer and side surfaces of the first layer, the third layer comprising a material having low leakage current properties.

31. (New) A semiconductor device according to claim 30, wherein the first layer comprises TiN.

32. (New) A semiconductor device according to claim 30, wherein the second layer comprises RuO<sub>2</sub>.

33. (New) A semiconductor device according to claim 30, wherein the third layer comprises Pt.

34. (New) A semiconductor device according to claim 30, wherein the conductive plug comprises polysilicon.

35. (New) A semiconductor device according to claim 30, wherein the insulating film exposed by the third layer is overetched.